



### **DUAL N-CHANNEL ENHANCEMENT MODE MOSFET**

# **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(on)max</sub>	I <sub>D</sub> T <sub>A</sub> = +25°C
20V	15.5mΩ @ $V_{GS}$ = 4.5 $V$	7.5A
	16.5mΩ @ $V_{GS}$ = 4.0V	7.3A
	19mΩ @ $V_{GS}$ = 3.1 $V$	6.9A
	$20m\Omega$ @ $V_{GS} = 2.5V$	6.7A
	$30m\Omega$ @ $V_{GS}$ = 1.8 $V$	5.4A

### **Description**

This new generation MOSFET has been designed to minimize the onstate resistance  $(R_{DS(ON)})$  and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

# **Applications**

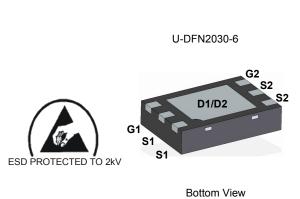
- Power Management Functions
- Battery Pack
- Load Switch

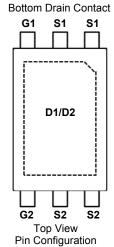
# **Features**

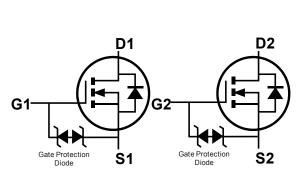
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

### **Mechanical Data**

- Case: U-DFN2030-6
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper leadframe. Solderable per MIL-STD-202, Method 208 (4)
- Weight: 0.012 grams (approximate)







# Ordering Information (Note 4)

Part Number	Case	Packaging
DMN2016LHAB-7	U-DFN2030-6	3,000 / Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

# **Marking Information**



26W = Product Type Marking Code YYWW = Date Code Marking YY = Last digit of year (ex: 12 for 2012) WW = Week code (01 to 53)



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Characte	Symbol	Value	Unit		
Drain-Source Voltage	$V_{DSS}$	20	V		
Gate-Source Voltage	V <sub>GSS</sub>	±12	V		
	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I <sub>D</sub>	7.5 5.8	А
Continuous Drain Current (Note 6) V <sub>GS</sub> = 4.5V	t < 10s	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I <sub>D</sub>	7.7 6.0	А
Pulsed Drain Current (10µs pulse, duty cycle = 1	I <sub>DM</sub>	45	А		

# **Thermal Characteristics**

Characteristic	Symbol	Value	Units		
Total Dawar Dissination (Note 5)	T <sub>A</sub> = +25°C	D	1.2	W	
Total Power Dissipation (Note 5)	T <sub>A</sub> = +70°C	P <sub>D</sub>	0.75	VV	
Thermal Peciatones Junction to Ambient (Note 5)	Steady State	D	106	°C/W	
Thermal Resistance, Junction to Ambient (Note 5)	t < 10s	$R_{\theta JA}$	100	C/VV	
Total Dowar Dissination (Note 6)	T <sub>A</sub> = +25°C	D	1.65	W	
Total Power Dissipation (Note 6)	T <sub>A</sub> = +70°C	P <sub>D</sub>	1	VV	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	D	78		
Thermal Resistance, Junction to Ambient (Note 6)	t < 10s	$R_{\theta JA}$	72	°C/W	
Thermal Resistance, Junction to Case	$R_{ heta JC}$	11.4			
Operating and Storage Temperature Range		T <sub>J.</sub> T <sub>STG</sub>	-55 to 150	°C	

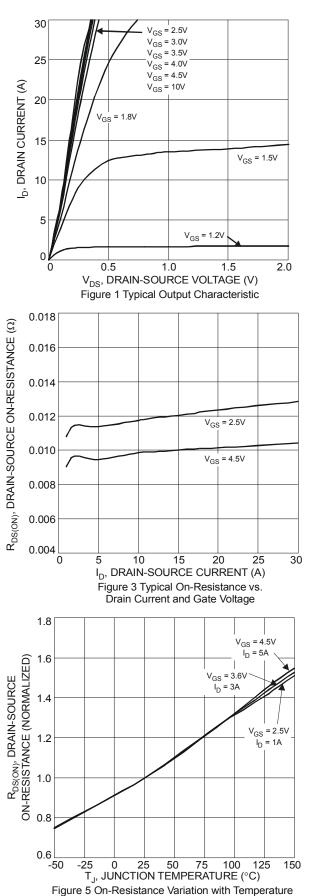
# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

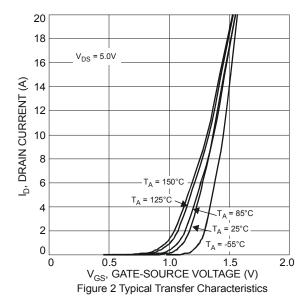
<u> </u>	· · ·						
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	20	_	_	V	$V_{GS} = 0V, I_{D} = 250\mu A$	
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	I <sub>DSS</sub>	_	_	1.0	μΑ	$V_{DS}$ = 20V, $V_{GS}$ = 0V	
Gate-Source Leakage	I <sub>GSS</sub>	-		±10	μΑ	$V_{GS} = \pm 8V$ , $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)	_	_	_				
Gate Threshold Voltage	V <sub>GS(th)</sub>	0.5	0.71	1.1	٧	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
			13	15.5	mΩ	$V_{GS} = 4.5V, I_D = 4.0A$	
			13.5	16.5		$V_{GS} = 4.0V, I_D = 4.0A$	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	_	14	19		$V_{GS} = 3.1V, I_D = 4.0A$	
	, ,		15	20		$V_{GS} = 2.5V, I_D = 4.0A$	
			21	30		$V_{GS} = 1.8V, I_D = 3.5A$	
Forward Transfer Admittance	Y <sub>fs</sub>	_	25	_	S	$V_{DS} = 5V, I_{D} = 6A$	
Diode Forward Voltage	V <sub>SD</sub>	_	0.75	1.0	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 1A	
DYNAMIC CHARACTERISTICS (Note 8)						•	
Input Capacitance	C <sub>iss</sub>	_	1550	_	pF		
Output Capacitance	Coss	_	166	_	pF	$V_{DS} = 10V, V_{GS} = 0V,$ - f = 1.0MHz	
Reverse Transfer Capacitance	Crss	_	145	_	pF	1 = 1.0WHZ	
Gate Resistance	Rq	_	1.37	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge (V <sub>GS</sub> = 2.5V)	Qq	_	8.4	_	nC		
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Qg	_	16	_	nC	)/ - 10\/   - 0A	
Gate-Source Charge	Q <sub>qs</sub>	_	2.3	_	nC	$V_{DS} = 10V, I_{D} = 6A$	
Gate-Drain Charge	$Q_{gd}$	_	2.5	_	nC		
Turn-On Delay Time	t <sub>D(on)</sub>	_	6.9	_	ns	$V_{DD} = 10V, R_L = 1.7\Omega,$ $V_{GS} = 5.0V, R_G = 3\Omega$	
Turn-On Rise Time	t <sub>r</sub>	_	15.5	_	ns		
Turn-Off Delay Time	$t_{D(off)}$	_	40.9	_	ns		
Turn-Off Fall Time	t <sub>f</sub>	_	12	_	ns		

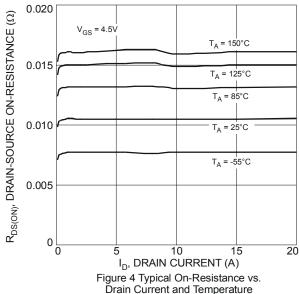
Notes:

- 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout
- Device mounted on FR-4 substrate PC board, 2oz copper, with 1 limital recommended p
   Repetitive rating, pulse width limited by junction temperature
   Guaranteed by design. Not subject to product testing



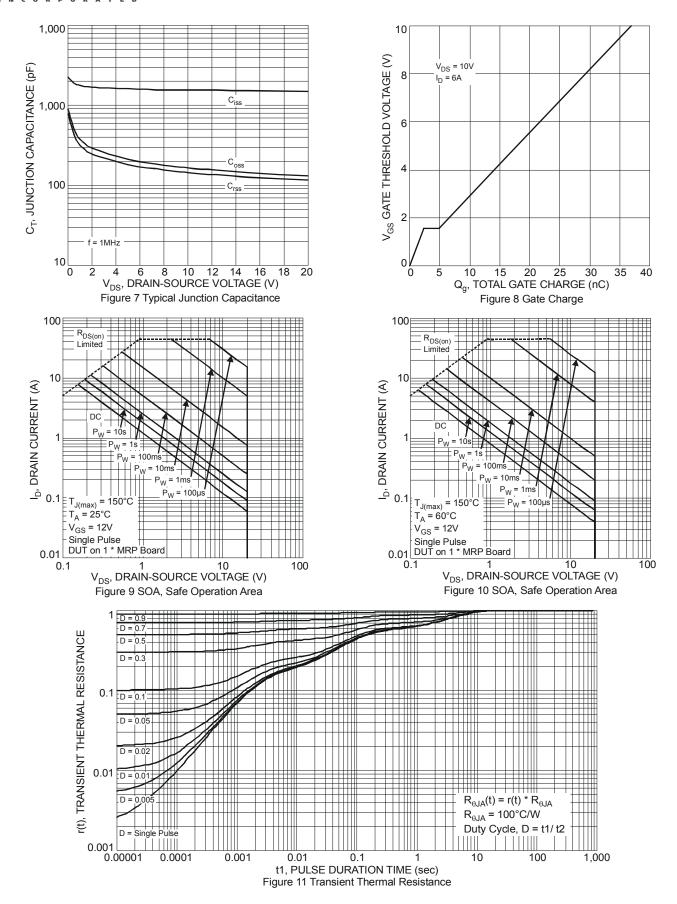






0.020  $R_{DS(ON)}$ , DRAIN-SOURCE ON-RESISTANCE  $(\Omega)$ 0.018  $V_{GS} = 2.5V$ I<sub>D</sub> = 1A 0.016 V<sub>GS</sub> = 3.6V 0.014 I<sub>D</sub> = 3A 0.012 V<sub>GS</sub> = 4.5V I<sub>D</sub> = 5A 0.010 0.008 0.006 0.004 100 25 50 75 T<sub>J</sub>, JUNCTION TEMPERATURE (°C) Figure 6 On-Resistance Variation with Temperature

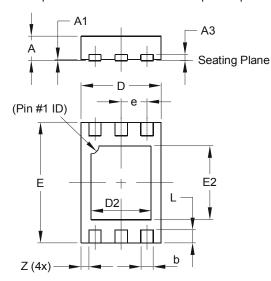






# **Package Outline Dimensions**

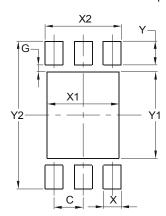
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



U-DFN2030-6							
Type B							
Dim	Min	Max	Тур				
Α	0.55	0.65	0.60				
<b>A</b> 1	0	0.05	0.02				
A3	-	-	0.15				
b	0.25	0.35	0.30				
D	1.95	2.05	2.00				
D2	1.40	1.60	1.50				
Е	2.95	3.05	3.00				
E2	1.74	1.94	1.84				
е	-	-	0.65				
L	0.28	0.38	0.33				
Ζ	-	-	0.20				
All Dimensions in mm							

# **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value			
Illiensions	(in mm)			
C	0.650			
G	0.150			
Х	0.400			
X1	1.600			
X2	1.700			
Y	0.530			
Y1	1.940			
Y2	3.300			



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